Date Mailed: April 30, 2008 Sheet 1 of I

FORM 1449* INFORMATION DISCLOSURE STATEMENT	Docket Number; 10873.1944USWO	Application Number: 10/598095	
IN AN APPLICATION	Applicant: KITAOKA, et al.		
(Use several sheets if necessary)	Filing Date: August 17, 2006	Group Art Unit: 1792	

		U.S	. PATENT DOCUME	NTS			
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING IF APPRO	
		FORE	IGN PATENT DOCUM	MENTS			
	DOCUMENT NO.	DATE	COUNTRY	CLASS SUBCLASS		TRANSL	ATION
						YES	NO
	2005/121415	December, 2005	WIPO				
2008-501600 January, 2008		January, 2008	Japan				
	отне	R DOCUMENTS (Including Author, Title,	Date, Pertiner	nt Pages, Etc.)		
	Introduction	Kawamura, et al., "Novel Liquid Phase Epitaxy (LPE) Growth Method for Growing Large GaN Single Crystals: Introduction of the Flux Film Coated-Liquid Phase Epitaxy (FFC-LPE) Method", Jpn. J. Appl. Phys. vol. 42 (2003), pp. L879-L881					

53148 Customer Number

	EXAMINER	DATE CONSIDERED
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.		